

# QPA4463A

DC to 3500MHz, CASCADABLE SiGe HBT MMIC AMPLIFIER

The QPA4463A is a high performance SiGe HBT MMIC amplifier. A Darlington configuration provides high  $F_T$  and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.



### SOT-363 Package

### **Features**

- DC to 3500MHz Operation
- Cascadable 50Ω

**Applications** 

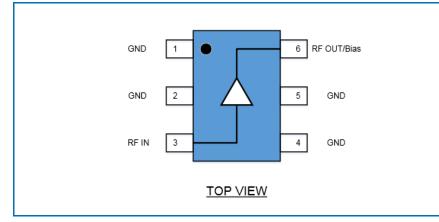
- Single Voltage Supply
- High Gain: 16.3 dB Typical at 1950 MHz
- Low Thermal Resistance Package

Power Amplifier Driver Amplifier

Cellular, PCS, GSM, UMTS

IF/RF Buffer Amplifier

Wireless Data, Satellite



## Functional Block Diagram

### **Ordering Information**

QPA4463ASQ	Sample Bag with 25 pieces
QPA4463ASR	7" Reel with 100 pieces
QPA4463ATR7	7" Reel with 3000 pieces
QPA4463APCK401	850MHz, +8V Operation PCBA with 5-piece Sample Bag

Revision DS20160204 © 2016 Qorvo, Inc.

# QPA4463A

# **Absolute Maximum Ratings**

Parameter	Rating	Units
Device Voltage(V <sub>D</sub> )	+5.0	V
Device Current (ID)	90	mA
RF Input Power Note 1	+18	dBm
Storage Temperature	-55 to +150	°C
ESD Rating (HBM)	TBD	-
Moisture Sensitivity Level	MSL1	-

Notes:

- 1. Load Condition 1:  $Z_L = 50 \Omega$
- Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in this table.
- 3. Bias Conditions should also satisfy the following expression:  $I_DV_D$  <(T\_J -T\_L)/  $R_{TH},$  and  $T_L$  =T\_LEAD.

# **Recommended Operating Conditions**

Parameter		Units			
Falameter	Min	Тур	Max	Units	
Operating Temperature Range	-40		+105	°C	
Junction Temperature (TJ)			+125	°C	
Device Operating Voltage	+2.9	+3.2	+3.5	V	

## **Electrical Specifications – General**

Devementer	S	Specification		Units	Conditions	
Parameter	Min	Тур	Max	Units	Conditions	
		18.3		dB	850MHz	
Small Signal Gain, S21		16.3		dB	1950MHz	
		15.6		dB	2400MHz	
		+15.0		dBm	850MHz	
Output Power at 1 dB Compression		+14.9		dBm	1950MHz	
		+14.9		dBm	2400MHz	
		+30.8		dBm	850MHz	
Output Third Order Intercept Point		+29.5		dBm	1950MHz	
		+28.6		dBm	2400MHz	
		20.5		dB	850MHz	
Input Return Loss, S11		17.3		dB	1950MHz	
		18.0		dB	2400MHz	
		36.0		dB	850MHz	
Output Return Loss, S22		13.2		dB	1950MHz	
		13.4		dB	2400MHz	
•	V <sub>D</sub> = +3.2 V, <sub>BIAS</sub> = 110Ω,				P3 Tone Spacing=1 MHz, $P_{OUT}$ per tone = -5 dBm,	

# rfmd 🔪 QOUVO

### RFMD + TriQuint = Qorvo



Caution! ESD sensitive device.



RFMD Green: RoHS status based on EU Directive 2011/65/EU (at time of this document revision), halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional - operation of the device under Absolute Maximum Rating conditions is not implied.



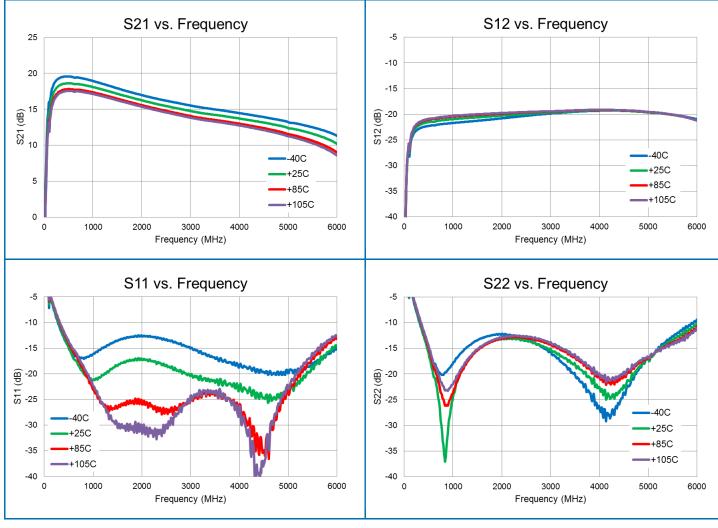


# QPA4463A

# **Electrical Specifications – General (Continued)**

Parameter	Specification			Units	Conditions
	Min	Тур	Мах	Units	Conditions
		21.1		dB	850MHz
Reverse Isolation, S12		20.3		dB	1950MHz
		20.0		dB	2400MHz
		2.7		dB	850MHz
Noise Figure		2.8		dB	1950MHz
		3.1		dB	2400MHz
Thermal Resistance		124		°C/W	
Device Operating Current		45.0		mA	
Test Conditions unless otherwise specified: $+V_D = +3.2 \text{ V}, V_S = +8 \text{ V}, I_D = 45 \text{ mA Typ.}, \text{ OIP3 Tone Spacing=1 MHz}, P_{OUT} \text{ per tone} = -5 \text{ dBm}, R_{BIAS} = 110\Omega, T_L = +25^{\circ}\text{C}, Z_S = Z_L = 50 \Omega$					

# **Typical Performance Using 850MHz Application Circuit**

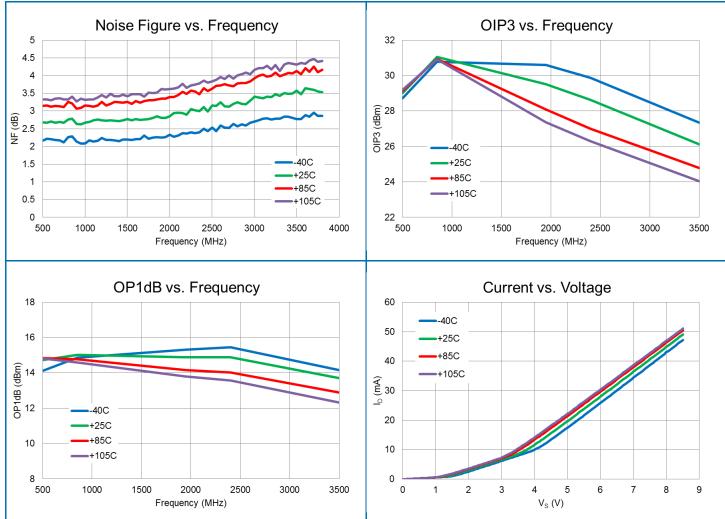


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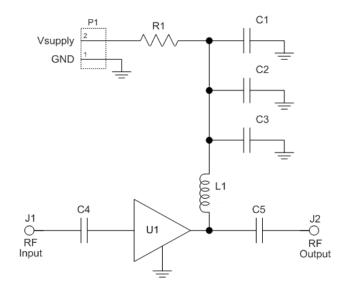




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### **Evaluation Board and Schematic**





# **Evaluation Board Bill of Materials For 850MHz Application Circuit**

Description	Reference Designator	Manufacturer	Manufacturer's P/N
Gain Block	U1	QORVO	QPA4463A
РСВ	NA	Viasystems Technologies Corp	QPAXX63X-410(A)
CAP, 1uF, 10%, 25V, X7R, 1206	C1	Murata Electronics	GRM31MR71E105KA01L
CAP, 1000pF, 10%, 50V, X7R, 0402	C2	Murata Electronics	GRM155R71H102KA01D
CAP, 68pF, 5%, 50V, C0G, 0402	C3	Murata Electronics	GRM1555C1H680JA01D
CAP, 100pF, 5%, 50V, C0G, 0402	C4, C5	Murata Electronics	GRM1555C1H101JA01D
RES, 110 OHM, 5%, 1/2W, 1210	R1	Panasonic Industrial Devices	ERJ-14YJ111U
IND, 33nH, 5%, M/L, 0603	L1	Murata Electronics	LL1608-FSL33NJ
CONN, SMA, EL, FLT, 0.068" SPE-000318	J1. J2	Amphenol RF Asia Corp	901-10426
CONN, HDR, ST, 1x2, 0.100", HI-TEMP, T/H	P1	Samtec Inc.	HTSW-102-07-G-S

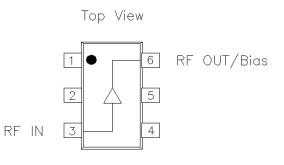


# QPA4463A

# **Component Values For Specific Frequency and Voltage in Application Circuit**

Reference	Frequency (MHz)							
Designator	500	850	1950	2400	3500			
C4, C5	220pF	100pF 68pF		56pF	39pF			
C <sub>3</sub>	100pF	68pF	22pF	22pF	15pF			
L <sub>1</sub>	68nH	33nH	22nH	18nH	15nH			
Required Bias Resistance for I <sub>D</sub> = 45mA Bias Resistance = R <sub>BIAS</sub> + R <sub>LDC</sub> = ( V <sub>S</sub> -V <sub>D</sub> ) / I <sub>D</sub>								
Supply Volt	tage (Vs)	+6 V	+8 V	+10 V	+12 V			
Bias Resistance (R <sub>1 =</sub> R <sub>Bias</sub> )		62 Ω 110 Ω		150 Ω	200 Ω			
Note: Bias resistor improves current stability over temperature								

# **Pin Configuration and Description**



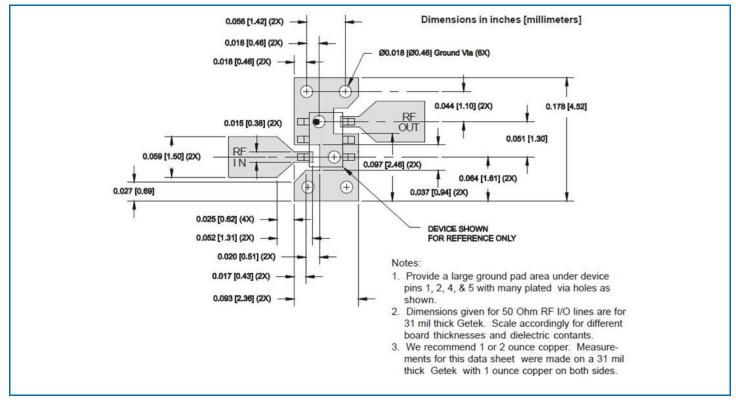
Pin	Label	Description
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor as shown in the application schematic.
1, 2, 4, 5	GND	Connect to ground per application circuit drawing. For best performance, vias should be used as shown in the recommended pad layout.
6	RF OUT/BIAS	RF output and bias pin. Bias will be supplied to this pin through an external RF choke. A DC blocking capacitor is necessary on the RF output as shown in the application circuit.



# QPA4463A

# Package Marking

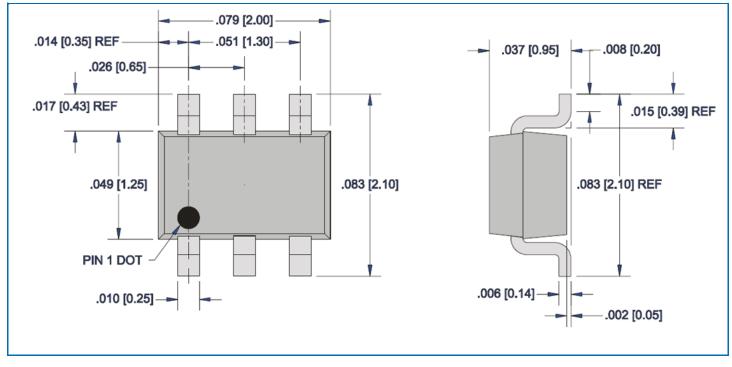
# Suggested Pad Layout (Dimensions in inches [millimeters])





# QPA4463A

Package Outline (Dimensions in inches [millimeters])



## **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.rfmd.com Tel: 1-844-890-8163 Email: customer.support@gorvo.com

For information about the merger of RFMD and TriQuint as Qorvo:

Web: www.qorvo.com

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